(iv)

"(f)   means for analyzing the collected, diffracted x-rays to map the 4P 3/17/10

lattice parameter in the polycrystalline material."

to:

(iv)

--(f)   means for analyzing the collected, diffracted x-rays;   4P 3/17/10

(v)

(g)   means for quantitatively mapping a lattice parameter in the 4P 3/17/10

polycrystalline material using said analyzed, collected, diffracted x-rays.--

Allowable Subject Matter

Claims 1-24 are allowed.

The following is an examiner's statement of reasons for allowance:

With respect to Claim 1, the prior art of record teaches many of the elements of

the claimed invention, including an x-ray diffraction method for the analysis of

polycrystalline materials, the method comprising: providing a polycrystalline material

sample for analysis; providing a polychromatic x-ray source, wherein the source

produces x-rays by accelerating charged particles to energies of no more than 1 MeV;

collimating x-rays from the polychromatic x-ray source into a beam having a divergence

in the range of from 10^{-4} to 10^{-2} radians; exposing at least a portion of the polycrystalline

material to the collimated x-ray beam, whereby the x-ray beam is diffracted; collecting at

least some of the diffracted x-rays in an energy dispersive x-ray detector or array; and,

analyzing the collected, diffracted x-rays to determine a lattice parameter in the

polycrystalline material.